NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE80H12H uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

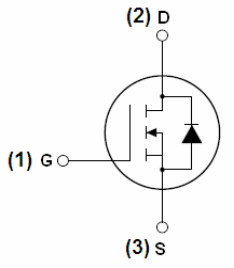
- V_{DS} =80V,I_D =120A
  $R_{DS(ON)}$ <6mΩ @ V_{GS}=10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

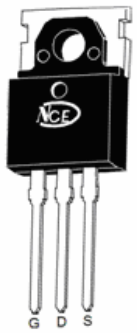
100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram

Marking and pin assignment



TO-220H-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE80H12H	NCE80H12H	TO-220H-3L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	120	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	84	A
Pulsed Drain Current	I_{DM}	450	A
Maximum Power Dissipation	P_D	220	W
Derating factor		1.47	W/℃

Single pulse avalanche energy (Note 5)	E_{AS}	1400	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	0.68	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

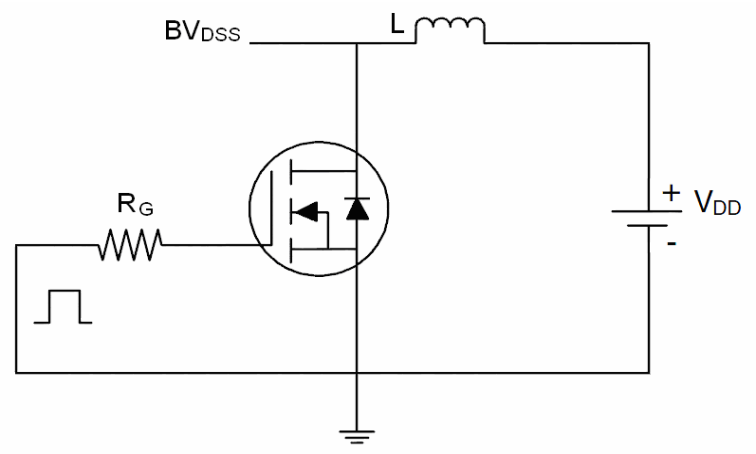
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	80	89	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=40A	-	4.9	6	mΩ
Forward Transconductance	g_{FS}	V_{DS}=25V,I_D=57A	90	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=25V,V_{GS}=0V, F=1.0MHz	-	6500	-	PF
Output Capacitance	C_{oss}		-	520	-	PF
Reverse Transfer Capacitance	C_{rss}		-	460	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V,I_D=2A V_{GS}=10V,R_G=2.5Ω	-	26	-	nS
Turn-on Rise Time	t_r		-	24	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	91	-	nS
Turn-Off Fall Time	t_f		-	39	-	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=30A, V_{GS}=10V	-	163		nC
Gate-Source Charge	Q_{gs}		-	31		nC
Gate-Drain Charge	Q_{gd}		-	64		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=40A	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	120	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF = 40A di/dt = 100A/μs (Note3)	-	42	60	nS
Reverse Recovery Charge	Qrr		-	66	80	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

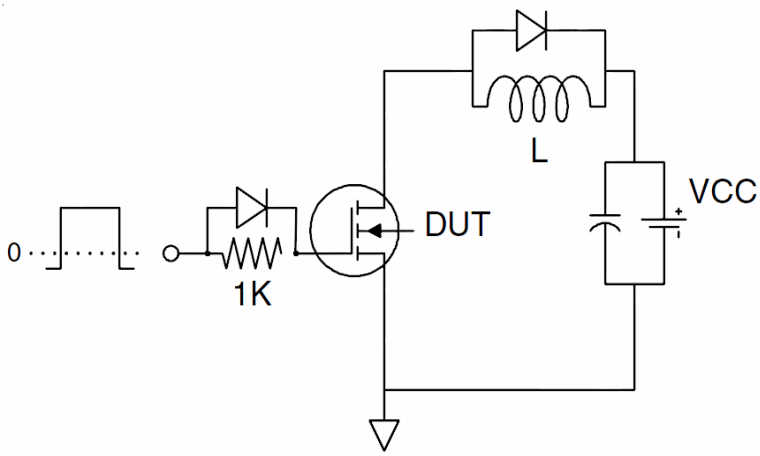
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition：Tj=25℃,V_{DD}=40V,V_G=10V,L=0.5mH,Rg=25Ω

Test circuit

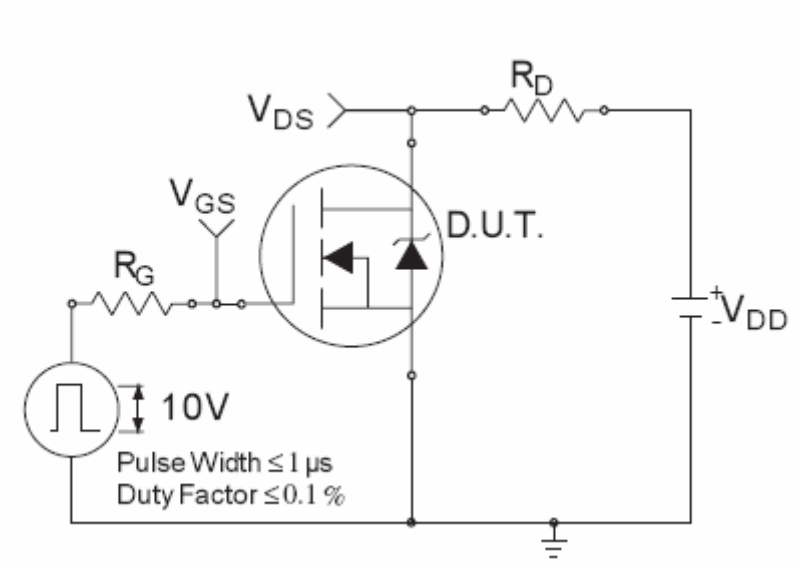
1）E_{AS} test Circuit



2）Gate charge test Circuit



3）Switch Time Test Circuit



T ypical Electrical and Thermal Characteristics (Curves)

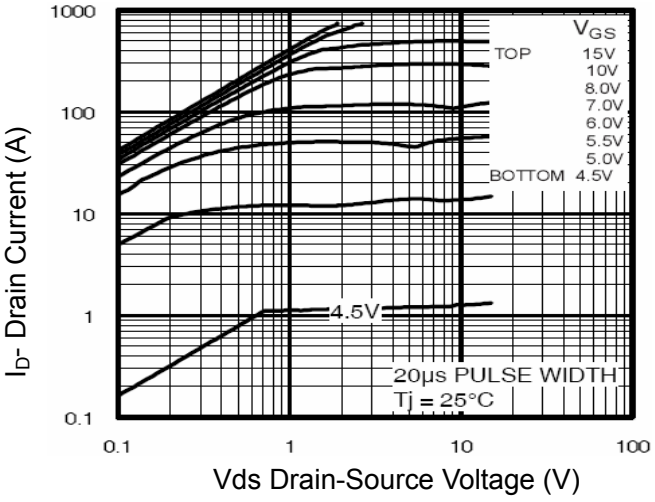


Figure 1 Output Characteristics

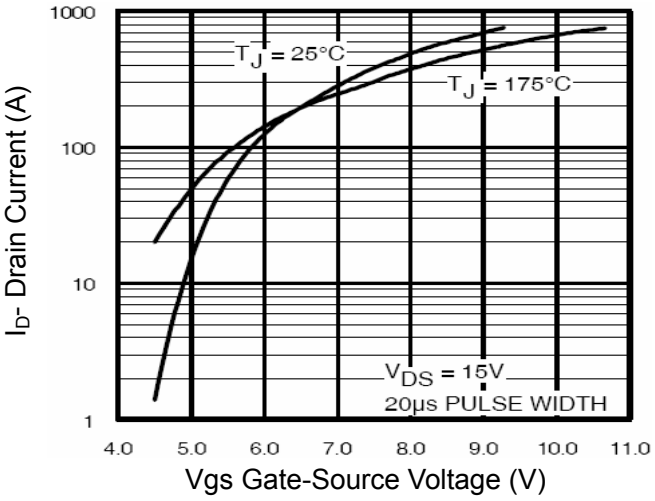


Figure 2 Transfer Characteristics

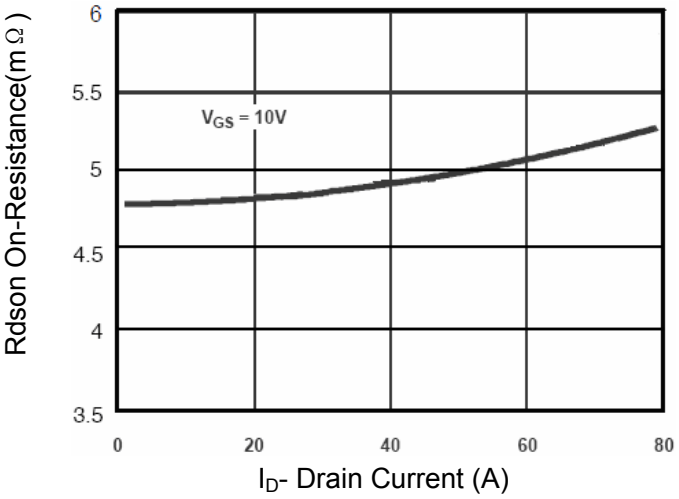


Figure 3 Rdson- Drain Current

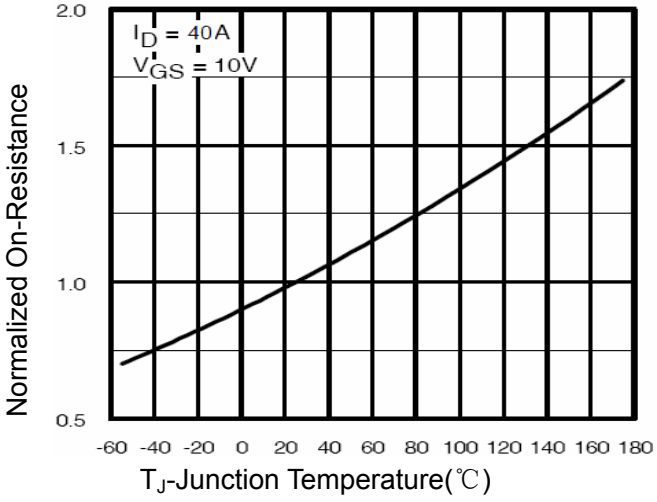


Figure 4 Rdson-JunctionTemperature

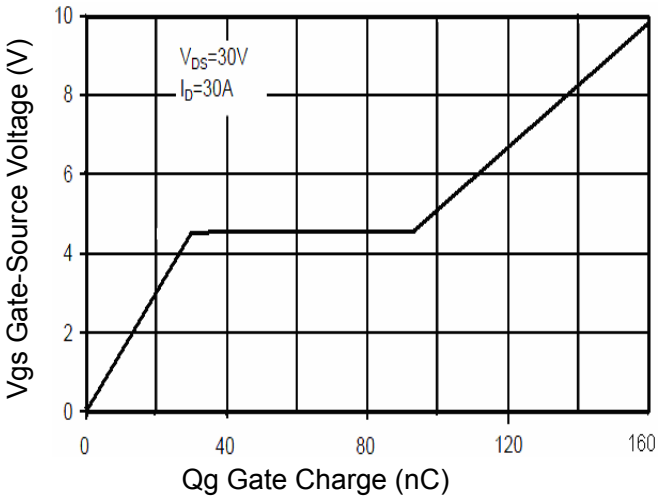


Figure 5 Gate Charge

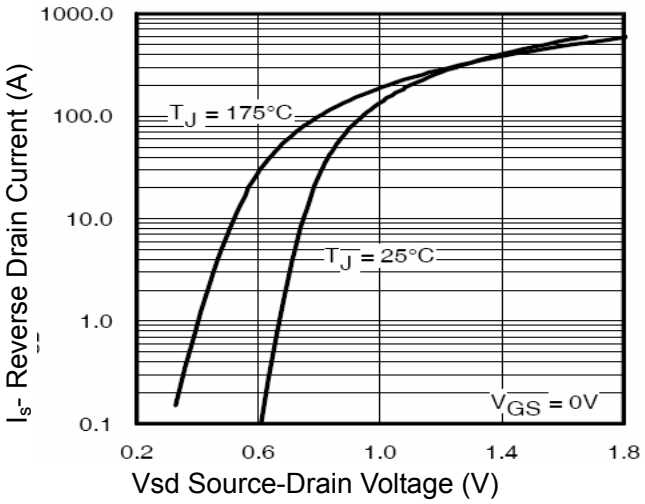


Figure 6 Source- Drain Diode Forward

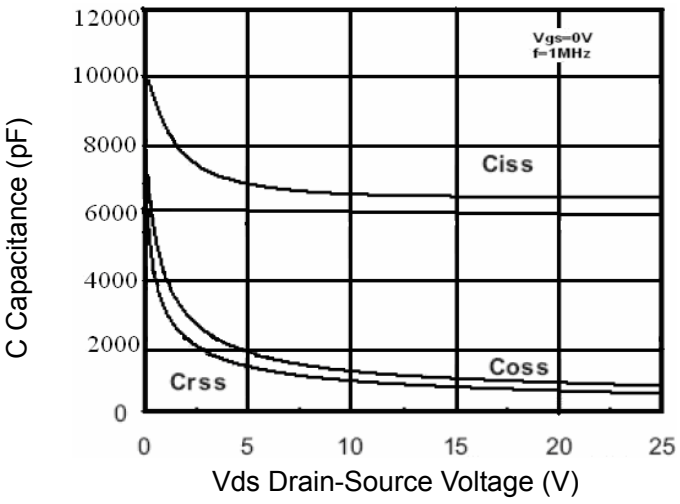


Figure 7 Capacitance vs Vds

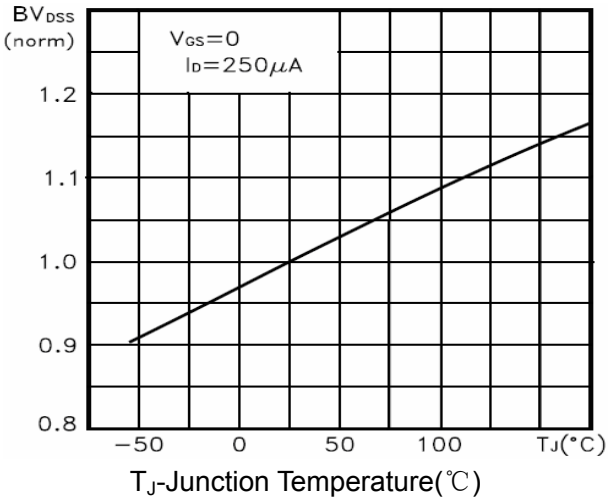


Figure 9 BV_{DSS} vs Junction Temperature

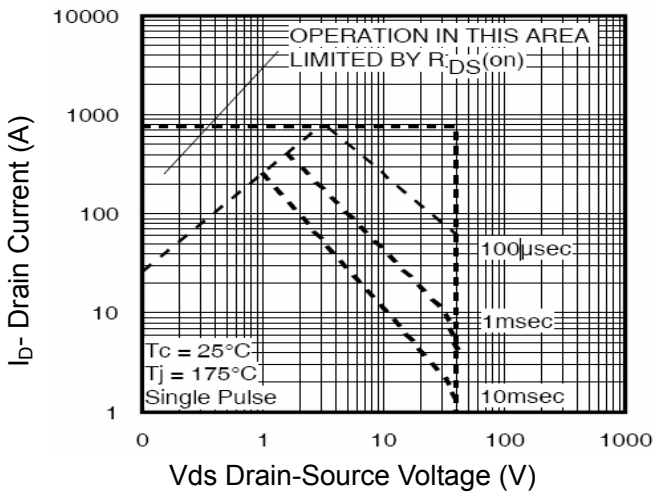


Figure 8 Safe Operation Area

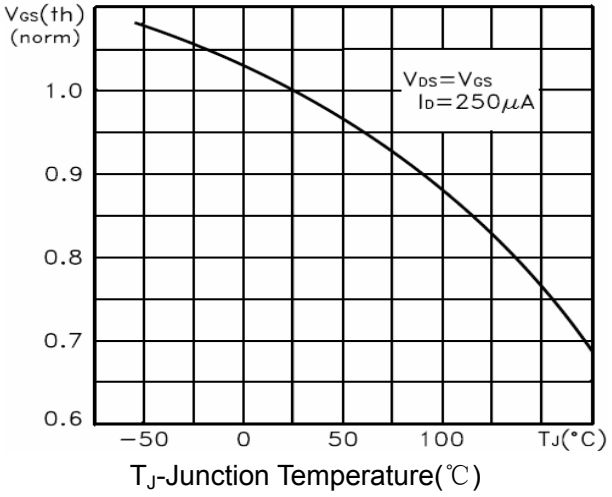


Figure 10 $V_{GS(th)}$ vs Junction Temperature

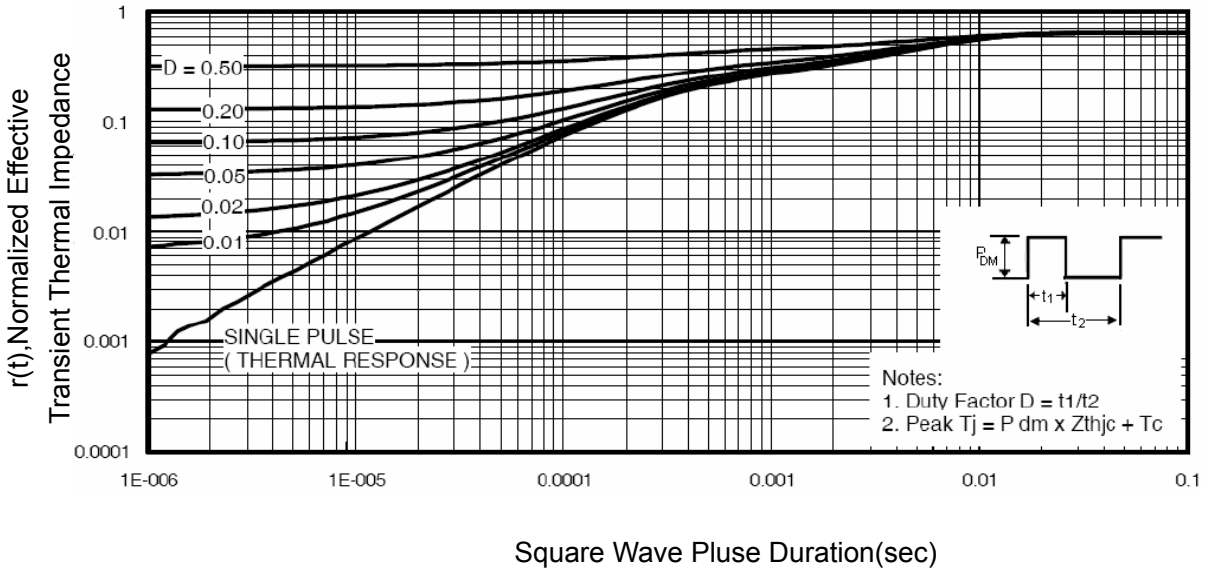
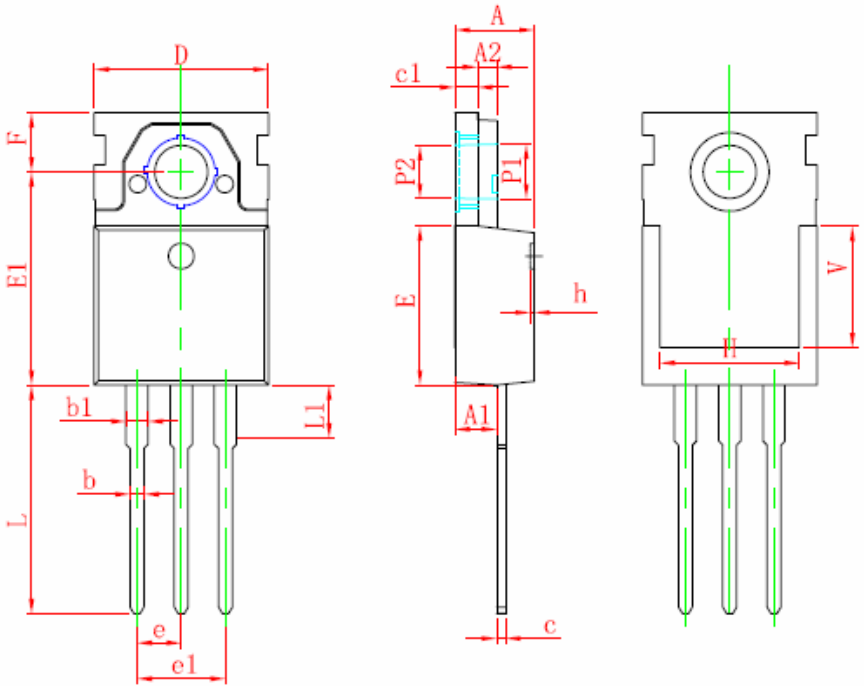


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220H-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
A2	1.000	1.200	0.039	0.047
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.820	10.220	0.387	0.402
E	8.950	9.350	0.352	0.368
E1	12.000	12.500	0.472	0.492
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	3.250	3.550	0.128	0.140
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.930	13.330	0.509	0.525
L1	3.450	3.850	0.136	0.152
P1	3.15 TYP.		0.124 TYP.	
P2	3.05 TYP.		0.120 TYP.	
V	6.900 REF.		0.272 REF.	

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